

# TN08N20SC

### N-Channel Enhancement Mode Power MOSFET

### **Features**

- $V_{DS}=20V$ ,  $R_{DS}@4.5V=14m\Omega$ ,  $I_{D}=8A$
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

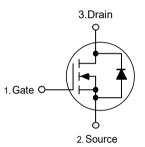
### **Application**

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



1. Gate 2. Source 3. Drain

### **Schematic Diagram**



### **Absolute Maximum Ratings**

Ratings at 25°C ambient temperature unless otherwise specified.

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	±12	V
I <sub>D</sub> @T <sub>c</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 4.5V	8.8	Α
I <sub>D</sub> @T <sub>c</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 4.5V	6.2	А
I <sub>DP</sub>	Pulsed Drain Current 4		Α
P <sub>D</sub> @T <sub>A</sub> =25℃	D@T <sub>A</sub> =25℃ Total Power Dissipation		W
T <sub>STG</sub>	T <sub>STG</sub> Storage Temperature Range -55 to 150		°C
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient		25	°C/W
Rthj-c	Maximum Thermal Resistance, Junction-case		8	°C/W

### **Electrical Characteristics**

(Ta=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃, I <sub>D</sub> =1mA		0.018		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}$ =4.5 $V$ , $I_D$ =6 $A$		8	13	mΩ
		V <sub>GS</sub> =2.5V , I <sub>D</sub> =5A		10	19	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250uA$	0.5		1.3	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =16V , V <sub>GS</sub> =0V.			10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 12V$ , $V_{DS}$ =0V			±100	nA
Qg	Total Gate Charge			16		
$Q_{gs}$	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =6A		3		nC
$Q_{gd}$	Gate-Drain Charge			4.5		
$T_{d(on)}$	Turn-On Delay Time			10		
Tr	Rise Time	V <sub>DS</sub> =10V , V <sub>GS</sub> =4.5V ,		13		no
T <sub>d(off)</sub>	Turn-Off Delay Time	$R_G=3.3\Omega$ $I_D=1A$		28		ns
T <sub>f</sub>	Fall Time			7		
C <sub>iss</sub>	Input Capacitance			1400		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		170		pF
$C_{rss}$	Reverse Transfer Capacitance			135		

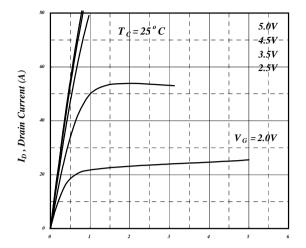
### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$V_{SD}$	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =1A			1.2	V
t <sub>rr</sub>	Reverse Recovery Time	IF=1A , V <sub>GS</sub> =0V,		8.5		nS
Q <sub>rr</sub>	Reverse Recovery Charge	dl/dt=100A/µs		2.5		nC

#### Notes:

- 1. Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in 2 copper pad of FR4 board, t  $\leq$ 10sec ; 60 °C/W at steady state.
- 4.Starting  $T_j{=}25^{\circ}C$  ,  $V_{DD}{=}20V$  , L=0.1mH ,  $R_G{=}25\Omega,\,V_{GS}{=}10V$

### **Typical Characteristics**



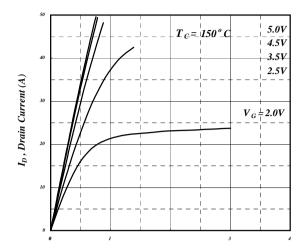
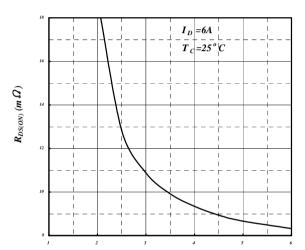


Fig 1. Typical Output Characteristics



rig 2. Typicai Output Characteristics

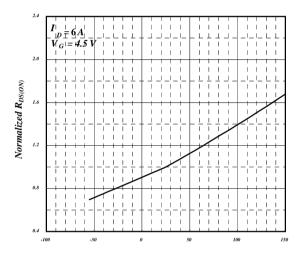


Fig 3. On-Resistance v.s. Gate Voltage

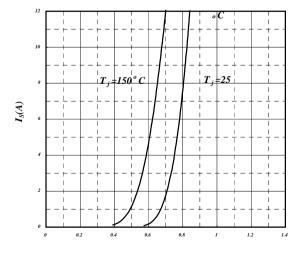


Fig 4. Normalized On-Resistance v.s. Junction Temperature

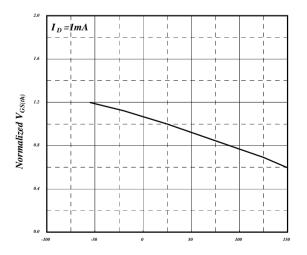


Fig 5. Forward Characteristic of Reverse Diode

Fig 6. Gate Threshold Voltage v.s. Junction Temperature

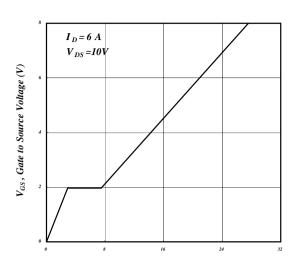


Fig 7. Gate Charge Characteristics

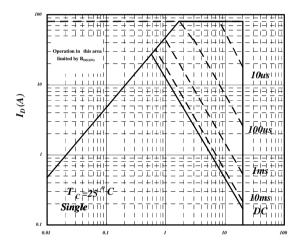


Fig 9. Maximum Safe Operating Area

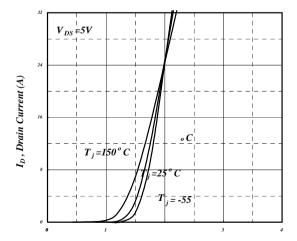


Fig 11. Transfer Characteristics

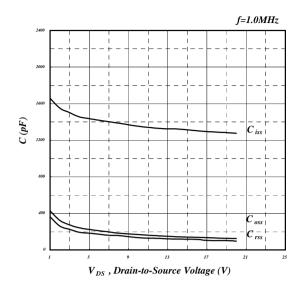
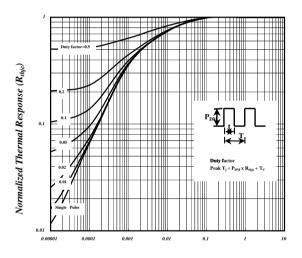


Fig 8. Typical Capacitance Characteristics



 ${\bf Fig~10.~Effective~Transient~Thermal~Impedance}$ 

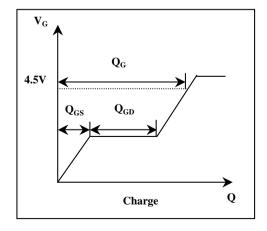


Fig 12. Gate Charge Waveform

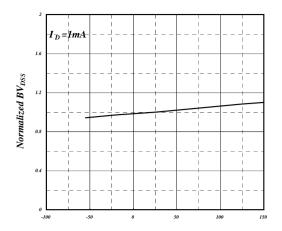


Fig 13. Normalized  $BV_{DSS}\,$  v.s. Junction Temperature

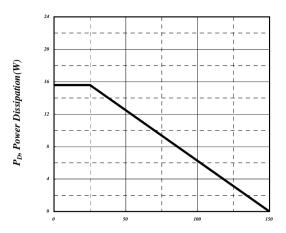


Fig 14. Total Power Dissipation

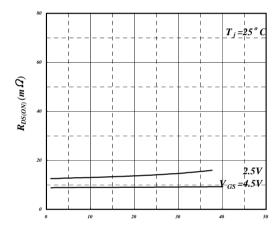
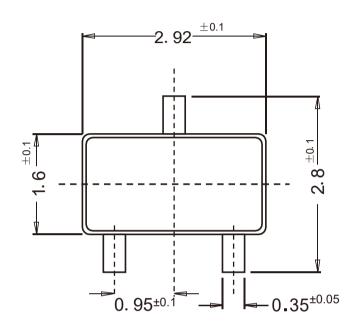


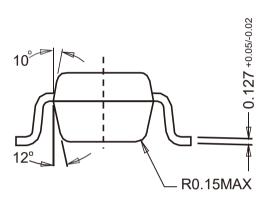
Fig 15. Typ. Drain-Source on State Resistance

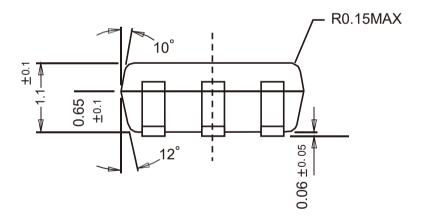
## **Package Outline**

SOT-23-3

Dimensions in mm





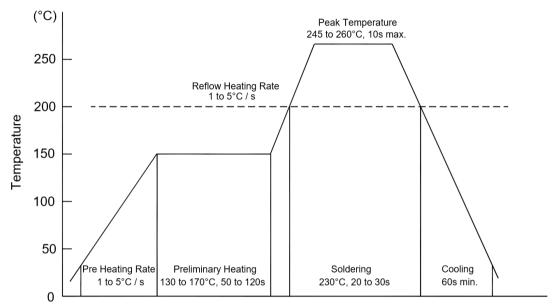


# **Ordering Information**

Device	Package	Shipping
TN08N20SC	SOT-23-3	3,000PCS/Reel&7inches

### **Conditions of Soldering and Storage**

### Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

### Conditions of hand soldering

• Temperature: 370 °C

Time: 3s max.Times: one time

### Storage conditions

Temperature

5 to 40 °C

Humidity

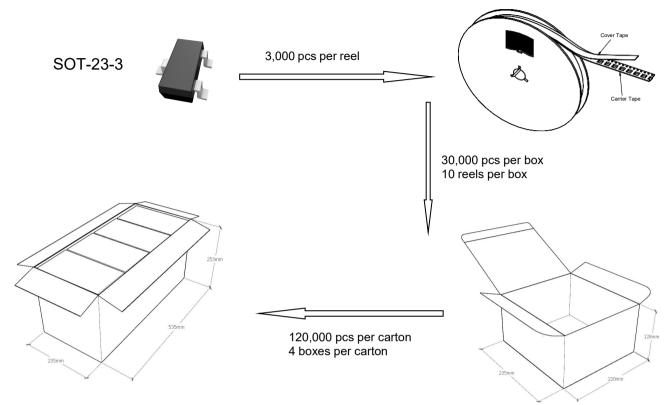
30 to 80% RH

Recommended period

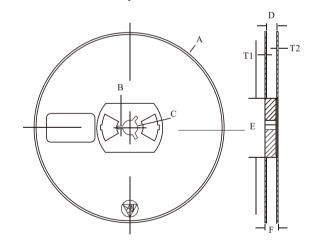
One year after manufacturing

## **Package Specifications**

• The method of packaging

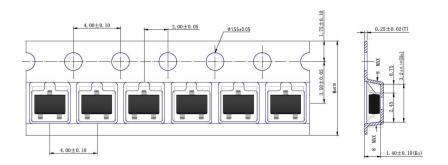


### ♦ Embossed tape and reel data



Symbol	Value (unit: mm)
Α	Ø 177.8±1
В	2.7±0.2
С	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

Reel (7")



#### **Contact Information**

TANI website: http://www.tanisemi.com Email:tani@tanisemi.com

For additional information, please contact your local Sales Representative.



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#### **Product Specification Statement**

The product specification aims to provide users with a reference regarding various product parameters, performance, and usage. It presents certain aspects of the product's performance in graphical form and is intended solely for users to select product and make product comparisons, enabling users to better understand and evaluate the characteristics and advantages of the product. It does not constitute any commitment, warranty, or guarantee.

The product parameters described in the product specification are numerical values, characteristics, and functions obtained through actual testing or theoretical calculations of the product in an independent or ideal state. Due to the complexity of product applications and variations in test conditions and equipment, there may be slight fluctuations in parameter test values. TANI shall not guarantee that the actual performance of the product when installed in the customer's system or equipment will be entirely consistent with the product specification, especially concerning dynamic parameters. It is recommended that users consult with professionals for product selection and system design. Users should also throughly validate and assess whether the actual parameters and performance when installed in their respective systems or equipment meet their requirements or expectations. Additionally, users should exercise caution in verifying product compatibility issues, and TANI assumes no responsibility for the application of the product. TANI strives to provide accurate and up-to-date information to the best of our ability. However, due to technical, human, or other reasons, TANI cannot guarantee that the information provided in the product specification is entirely accurate and error-free. TANI shall not be held responsible for any losses or damages resulting from the use or reliance on any information in these product specifications.

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Users are advised to pay attention to the parameter limit values specified in the product specification and maintain a certain margin in design or application to ensure that the product does not exceed the parameter limit values defined in the product specification. This precaution should be taken to avoid exceeding one or more of the limit values, which may result in permanent irreversible damage to the product, ultimately affecting the quality and reliability of the system or equipment.

The design of the product is intended to meet civilian needs and is not guaranteed for use in harsh environments or precision equipment. It is not recommended for use in systems or equipment such as medical devices, aircraft, nuclear power, and similar systems, where failures in these systems or equipment could reasonably be expected to result in personal injury. TANI shall assume no responsibility for any consequences resulting from such usage.

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